

Michael Yakimov

List of Publications by Year in descending order

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docs citations

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citing authors

#	ARTICLE	IF	CITATIONS
1	Drain-Voltage-Induced Secondary Effects in AlGaIn/GaN HEMTs With Integrated Body-Diode. IEEE Transactions on Electron Devices, 2020, 67, 3983-3987.	3.0	6
2	Anomalous minority carrier behavior induced by chemical surface passivation solution in p-type GaSb metal-oxide-semiconductor capacitors on Si substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, 052204.	1.2	0
3	Dynamic Control of AlGaIn/GaN HEMT Characteristics by Implementation of a p-GaN Body-Diode-Based Back-Gate. IEEE Journal of the Electron Devices Society, 2019, 7, 581-588.	2.1	16
4	Integrated Semiconductor Quantum Dot Scintillation Detector: Ultimate Limit for Speed and Light Yield. IEEE Transactions on Nuclear Science, 2016, 63, 656-663.	2.0	7
5	Group III-Sb Metamorphic Buffer on Si for p-Channel all-III-V CMOS: Electrical Properties, Growth and Surface Defects. Materials Research Society Symposia Proceedings, 2015, 1790, 13-18.	0.1	0
6	Development of III-Sb Technology for p-Channel MOSFETs. , 2015, , .		1
7	Interface trap density and mobility extraction in InGaAs buried quantum well metal-oxide-semiconductor field-effect-transistors by gated Hall method. Applied Physics Letters, 2014, 104, .	3.3	5
8	Development of III-Sb Technology for p-Channel MOSFETs. International Journal of High Speed Electronics and Systems, 2014, 23, 1450015.	0.7	4
9	GaSb on Si: Structural Defects and Their Effect on Surface Morphology and Electrical Properties. Materials Research Society Symposia Proceedings, 2014, 1635, 115-120.	0.1	5
10	Investigation of arsenic and antimony capping layers, and half cycle reactions during atomic layer deposition of Al ₂ O ₃ on GaSb(100). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	10
11	Hole mobility and remote scattering in strained InGaSb quantum well MOSFET channels with Al ₂ O ₃ oxide. Physica Status Solidi - Rapid Research Letters, 2013, 7, 550-553.	2.4	5
12	Improvement of the GaSb/Al ₂ O ₃ interface using a thin InAs surface layer. Solid-State Electronics, 2012, 78, 56-61.	1.4	30
13	Electron Scattering in Buried InGaAs/High-k MOS Channels. ECS Transactions, 2011, 35, 385-395.	0.5	10
14	In Situ Deposited HfO ₂ with Amorphous-Si Passivation as a Potential Gate Stack for High Mobility (In)GaSb- Based P-MOSFETs. ECS Transactions, 2011, 41, 223-230.	0.5	11
15	Exciton-lattice polaritons in multiple-quantum-well-based photonic crystals. Nature Photonics, 2009, 3, 662-666.	31.4	64
16	CHALLENGES AND PROGRESS IN III-V MOSFETs FOR CMOS CIRCUITS. Selected Topics in Electornics and Systems, 2009, , 3-14.	0.2	1
17	Strained Quantum Wells for P-channel InGaAs CMOS. Materials Research Society Symposia Proceedings, 2008, 1108, 1.	0.1	2
18	CHALLENGES AND PROGRESS IN III-V MOSFETs FOR CMOS CIRCUITS. International Journal of High Speed Electronics and Systems, 2008, 18, 761-772.	0.7	7

#	ARTICLE	IF	CITATIONS
19	InGaAs and GaAs/InGaAs Channel Enhancement Mode n-MOSFETs With HfO ₂ Gate Oxide and a-Si Interface Passivation Layer. Device Research Conference, IEEE Annual, 2007, , .	0.0	1
20	Tunnel QW-QDs InGaAs-InAs High Gain Medium for All-Epitaxial VCSELs. Materials Research Society Symposia Proceedings, 2006, 959, 1.	0.1	0
21	Optical properties of InAs quantum dot structures transferred to Si with oxidation lift-off technology. , 2006, , .		0
22	In situ monitoring of formation of InAs quantum dots and overgrowth by GaAs or AlAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1221.	1.6	12
23	Structural and Optical Effects of Capping Layer Material and Growth Rate on the Properties of Self-Assembled InAs Quantum Dot Structures. Materials Research Society Symposia Proceedings, 2004, 829, 142.	0.1	5